

# DATA SHEET

## **BTA216 series D, E and F** Three quadrant triacs guaranteed commutation

Product specification

September 2018

# Three quadrant triacs guaranteed commutation

## BTA216 series D, E and F

### GENERAL DESCRIPTION

Passivated guaranteed commutation triacs in a plastic envelope intended for use in motor control circuits or with other highly inductive loads. These devices balance the requirements of commutation performance and gate sensitivity. The "sensitive gate" E series and "logic level" D series are intended for interfacing with low power drivers, including micro controllers.

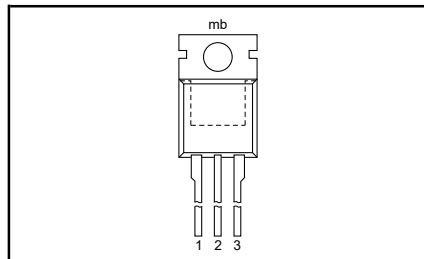
### QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
$V_{DRM}$	Repetitive peak off-state voltages	<b>600D</b> <b>600E</b> <b>600F</b> 600	V
$I_{T(RMS)}$	RMS on-state current	16	A
$I_{TSM}$	Non-repetitive peak on-state current	140	A

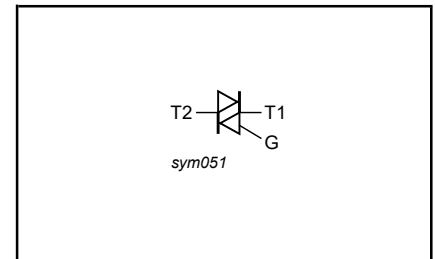
### PINNING - TO220AB

PIN	DESCRIPTION
1	main terminal 1
2	main terminal 2
3	gate
tab	main terminal 2

### PIN CONFIGURATION



### SYMBOL



### LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{DRM}$	Repetitive peak off-state voltages		-	600 <sup>1</sup>	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 99\text{ }^\circ\text{C}$	-	16	A
$I_{TSM}$	Non-repetitive peak on-state current	full sine wave; $T_j = 25\text{ }^\circ\text{C}$ prior to surge $t = 20\text{ ms}$	-	140	A
$I^2t$	$I^2t$ for fusing	$t = 16.7\text{ ms}$	-	150	A
$di_T/dt$	Repetitive rate of rise of on-state current after triggering	$t = 10\text{ ms}$ $I_{TM} = 20\text{ A}; I_G = 0.2\text{ A};$ $di_G/dt = 0.2\text{ A}/\mu\text{s}$	-	98	A <sup>2</sup> s
$I_{GM}$	Peak gate current		-	2	A
$P_{GM}$	Peak gate power		-	5	W
$P_{G(AV)}$	Average gate power	over any 20 ms period	-	0.5	W
$T_{stg}$	Storage temperature		-40	150	°C
$T_j$	Operating junction temperature		-	125	°C

<sup>1</sup> Although not recommended, off-state voltages up to 800V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 15 A/μs.

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### THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th\ j-mb}$	Thermal resistance junction to mounting base	full cycle	-	-	1.2	K/W
$R_{th\ j-a}$	Thermal resistance junction to ambient	half cycle in free air	-	-	1.7	K/W
			-	60	-	K/W

### STATIC CHARACTERISTICS

$T_j = 25\text{ °C}$  unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.			UNIT
		<b>BTA216-</b>		<b>...D</b>	<b>...E</b>	<b>...F</b>	
$I_{GT}$	Gate trigger current <sup>2</sup>	$V_D = 12\text{ V}; I_T = 0.1\text{ A}$ T2+ G+ T2+ G- T2- G-	-	5	10	25	mA
$I_L$	Latching current	$V_D = 12\text{ V}; I_{GT} = 0.1\text{ A}$ T2+ G+ T2+ G- T2- G-	-	15	25	30	mA
$I_H$	Holding current	$V_D = 12\text{ V}; I_{GT} = 0.1\text{ A}$	-	15	25	30	mA
$V_T$	On-state voltage	$I_T = 20\text{ A}$	-	1.5			V
$V_{GT}$	Gate trigger voltage	$V_D = 12\text{ V}; I_T = 0.1\text{ A}$ $V_D = 400\text{ V}; I_T = 0.1\text{ A};$ $T_j = 125\text{ °C}$	0.25	1.5			V
$I_D$	Off-state leakage current	$V_D = V_{DRM(max)}; T_j = 125\text{ °C}$	-	0.5			mA

### DYNAMIC CHARACTERISTICS

$T_j = 25\text{ °C}$  unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.			MAX.	UNIT
		<b>BTA216-</b>	<b>...D</b>	<b>...E</b>	<b>...F</b>		
$dV_D/dt$	Critical rate of rise of off-state voltage	$V_{DM} = 67\% V_{DRM(max)};$ $T_j = 110\text{ °C};$ exponential waveform; gate open circuit	30	60	70	-	V/ $\mu$ s
$dI_{com}/dt$	Critical rate of change of commutating current	$V_{DM} = 400\text{ V}; T_j = 125\text{ °C};$ $I_{T(RMS)} = 16\text{ A};$ $dV_{com}/dt = 10\text{ V}/\mu\text{s};$ gate open circuit	2.5	6.2	18	-	A/ms
$dI_{com}/dt$	Critical rate of change of commutating current	$V_{DM} = 400\text{ V}; T_j = 125\text{ °C};$ $I_{T(RMS)} = 16\text{ A};$ $dV_{com}/dt = 0.1\text{ V}/\mu\text{s};$ gate open circuit	12	20	50	-	A/ms

<sup>2</sup> Device does not trigger in the T2-, G+ quadrant.

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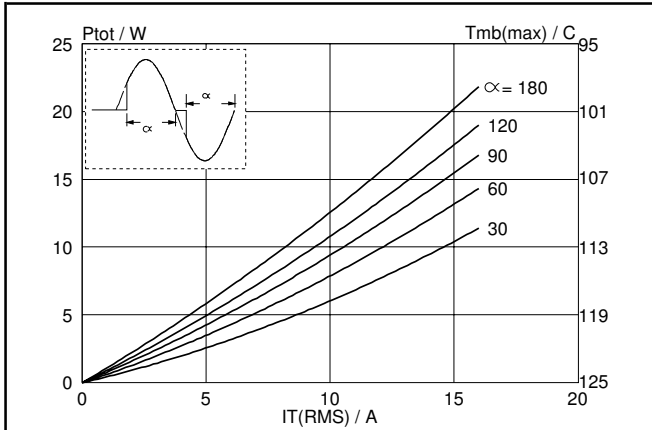


Fig.1. Maximum on-state dissipation,  $P_{tot}$ , versus rms on-state current,  $I_{T(RMS)}$ , where  $\alpha$  = conduction angle.

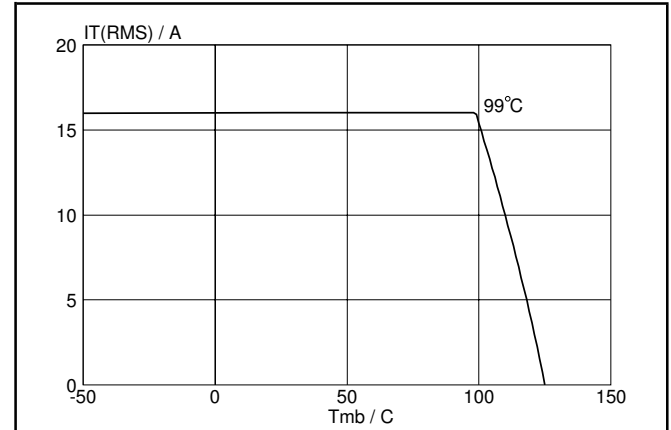


Fig.4. Maximum permissible rms current  $I_{T(RMS)}$ , versus mounting base temperature  $T_{mb}$ .

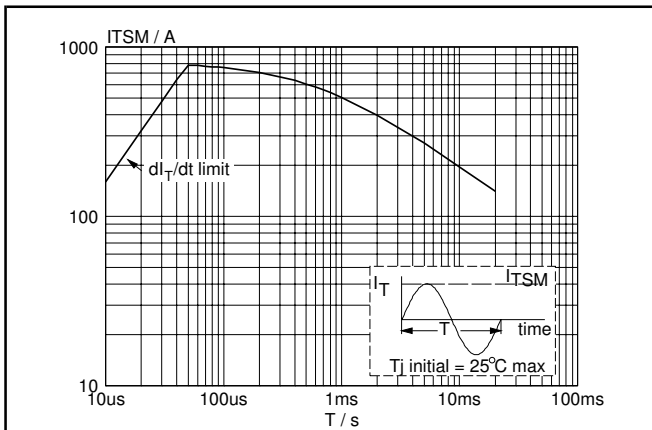


Fig.2. Maximum permissible non-repetitive peak on-state current  $I_{TSM}$ , versus pulse width  $t_p$ , for sinusoidal currents,  $t_p \leq 20\text{ms}$ .

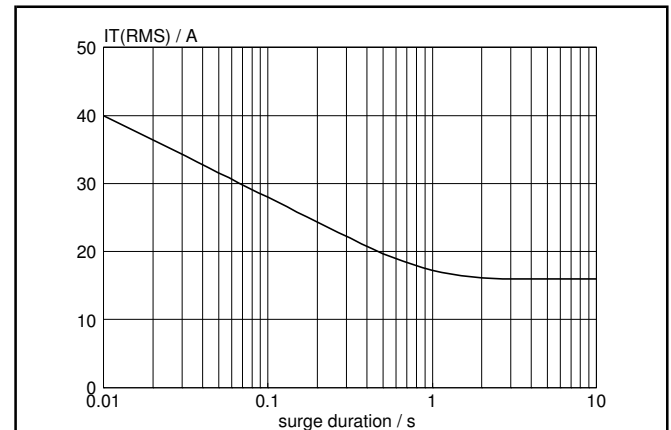


Fig.5. Maximum permissible repetitive rms on-state current  $I_{T(RMS)}$ , versus surge duration, for sinusoidal currents,  $f = 50\text{ Hz}$ ;  $T_{mb} \leq 99^\circ\text{C}$ .

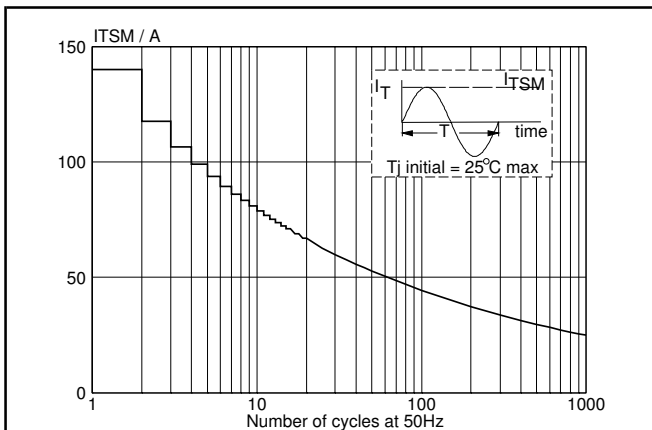


Fig.3. Maximum permissible non-repetitive peak on-state current  $I_{TSM}$ , versus number of cycles, for sinusoidal currents,  $f = 50\text{ Hz}$ .

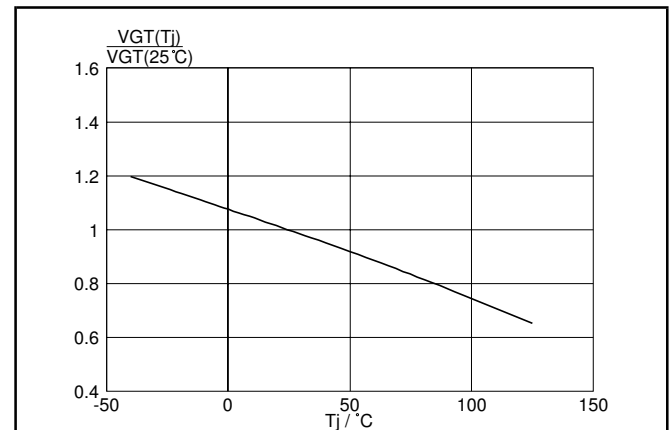
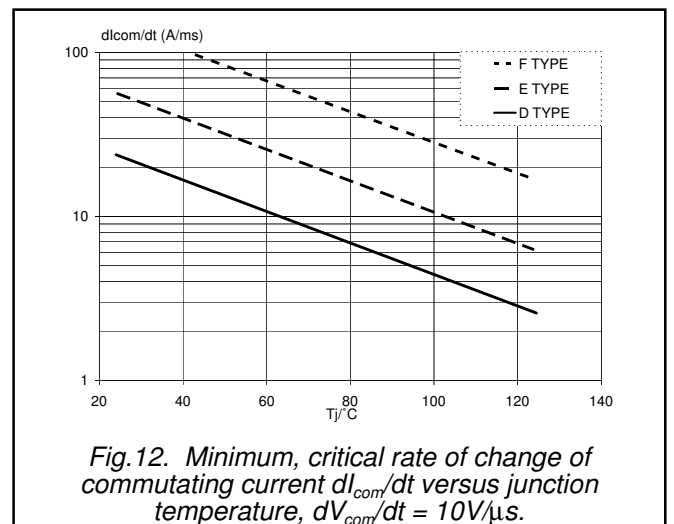
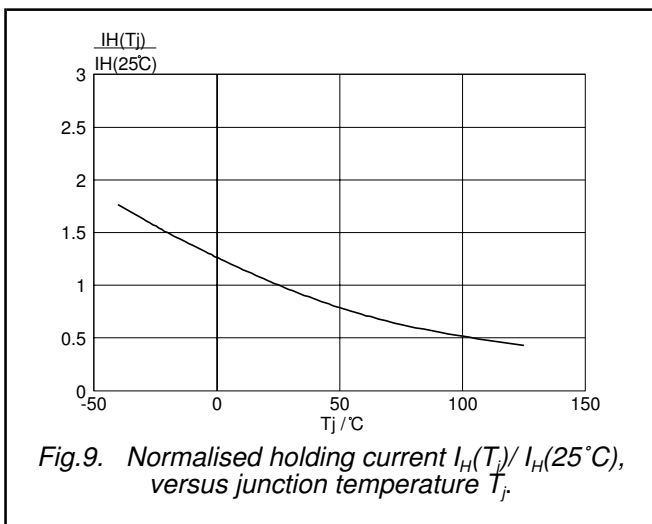
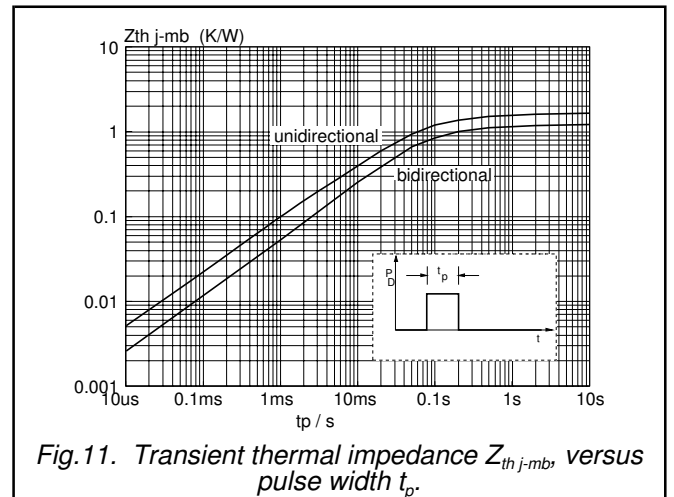
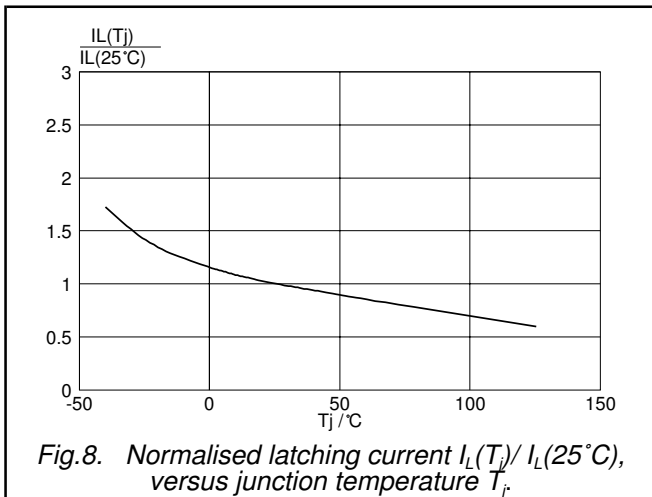
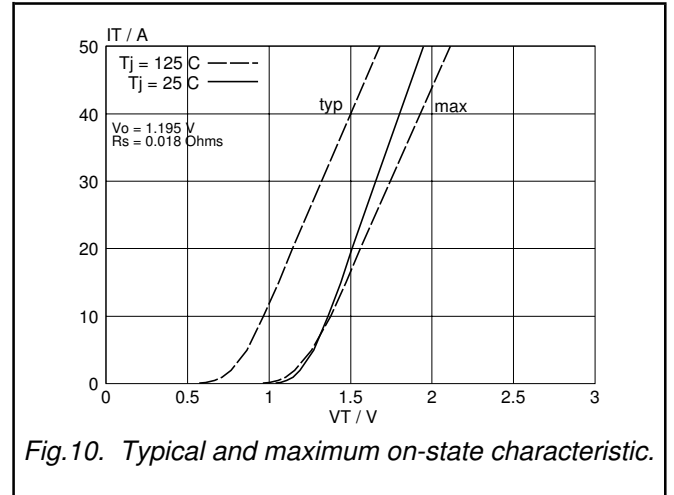
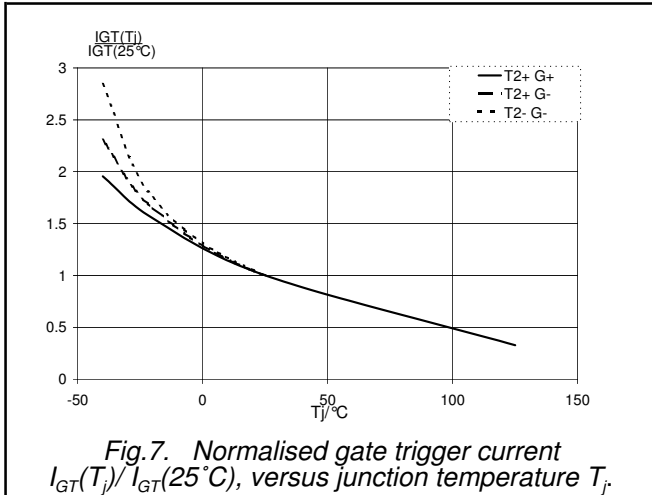


Fig.6. Normalised gate trigger voltage  $V_{GT}(T_j) / V_{GT}(25^\circ\text{C})$ , versus junction temperature  $T_j$ .

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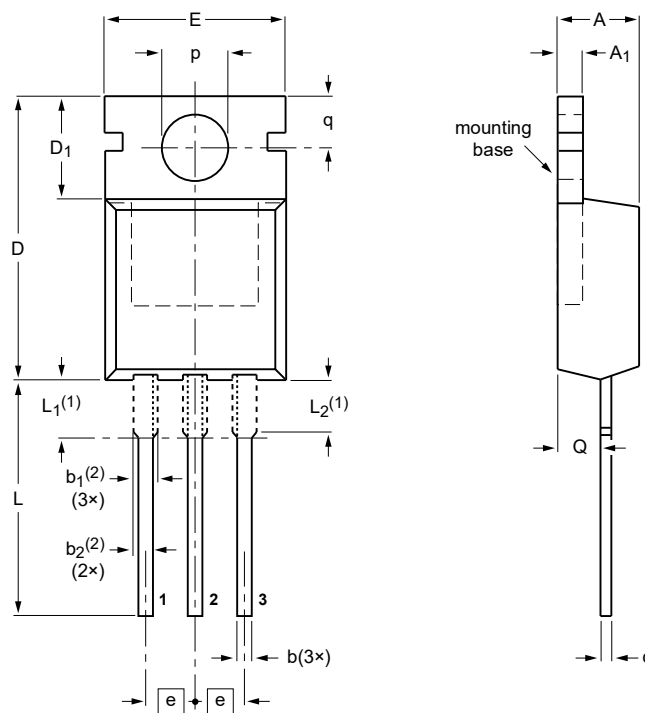
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**MECHANICAL DATA**

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78



**DIMENSIONS (mm are the original dimensions)**

UNIT	A	A <sub>1</sub>	b	b <sub>1</sub> ( <sup>2</sup> )	b <sub>2</sub> ( <sup>2</sup> )	c	D	D <sub>1</sub>	E	e	L	L <sub>1</sub> ( <sup>1</sup> )	L <sub>2</sub> ( <sup>1</sup> ) max.	p	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

**Notes**

1. Lead shoulder designs may vary.
2. Dimension includes excess dambar.

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
SOT78		3-lead TO-220AB	SC-46		08-04-23 08-06-13

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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